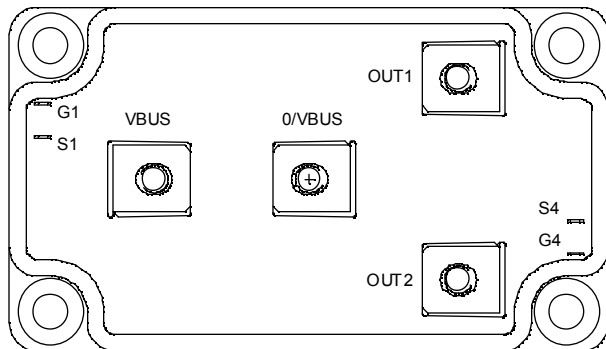
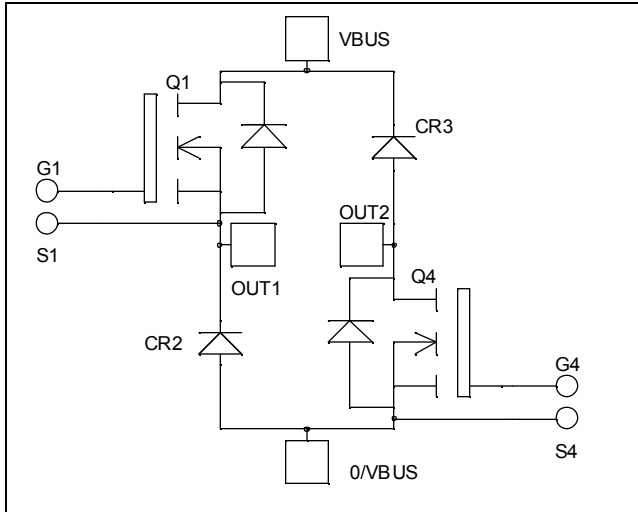


## Asymmetrical - Bridge MOSFET Power Module

$$V_{DSS} = 100V$$

$$R_{DS(on)} = 4.5m\Omega \text{ typ @ } T_j = 25^\circ C$$

$$I_D = 278A \text{ @ } T_c = 25^\circ C$$



### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Power MOS V<sup>®</sup> MOSFETs
  - Low  $R_{DS(on)}$
  - Low input and Miller capacitance
  - Low gate charge
  - Avalanche energy rated
  - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
  - Symmetrical design
  - M5 power connectors
- High level of integration

### Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile
- RoHS Compliant

### Absolute maximum ratings

| Symbol       | Parameter                                         | Max ratings                                            | Unit       |
|--------------|---------------------------------------------------|--------------------------------------------------------|------------|
| $V_{DSS}$    | Drain - Source Breakdown Voltage                  | 100                                                    | V          |
| $I_D$        | Continuous Drain Current                          | $T_c = 25^\circ C$<br>278<br>$T_c = 80^\circ C$<br>207 | A          |
| $I_{DM}$     | Pulsed Drain current                              | 1100                                                   |            |
| $V_{GS}$     | Gate - Source Voltage                             | $\pm 30$                                               | V          |
| $R_{DS(on)}$ | Drain - Source ON Resistance                      | 5                                                      | m $\Omega$ |
| $P_D$        | Maximum Power Dissipation                         | $T_c = 25^\circ C$<br>780                              | W          |
| $I_{AR}$     | Avalanche current (repetitive and non repetitive) | 100                                                    | A          |
| $E_{AR}$     | Repetitive Avalanche Energy                       | 50                                                     | mJ         |
| $E_{AS}$     | Single Pulse Avalanche Energy                     | 3000                                                   |            |



**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

| Symbol       | Characteristic                  | Test Conditions                 | Min | Typ | Max       | Unit      |
|--------------|---------------------------------|---------------------------------|-----|-----|-----------|-----------|
| $I_{DSS}$    | Zero Gate Voltage Drain Current | $V_{GS} = 0V, V_{DS} = 100V$    |     |     | 200       | $\mu A$   |
|              |                                 | $V_{GS} = 0V, V_{DS} = 80V$     |     |     | 1000      |           |
| $R_{DS(on)}$ | Drain – Source on Resistance    | $V_{GS} = 10V, I_D = 125A$      |     | 4.5 | 5         | $m\Omega$ |
| $V_{GS(th)}$ | Gate Threshold Voltage          | $V_{GS} = V_{DS}, I_D = 5mA$    | 2   |     | 4         | V         |
| $I_{GSS}$    | Gate – Source Leakage Current   | $V_{GS} = \pm 30V, V_{DS} = 0V$ |     |     | $\pm 200$ | nA        |

**Dynamic Characteristics**

| Symbol       | Characteristic               | Test Conditions                                                                                                                       | Min | Typ  | Max | Unit |
|--------------|------------------------------|---------------------------------------------------------------------------------------------------------------------------------------|-----|------|-----|------|
| $C_{iss}$    | Input Capacitance            | $V_{GS} = 0V$                                                                                                                         |     | 20   |     | nF   |
| $C_{oss}$    | Output Capacitance           | $V_{DS} = 25V$                                                                                                                        |     | 8    |     |      |
| $C_{rss}$    | Reverse Transfer Capacitance | $f = 1MHz$                                                                                                                            |     | 2.9  |     |      |
| $Q_g$        | Total gate Charge            | $V_{GS} = 10V$                                                                                                                        |     | 700  |     | nC   |
| $Q_{gs}$     | Gate – Source Charge         | $V_{Bus} = 50V$                                                                                                                       |     | 120  |     |      |
| $Q_{gd}$     | Gate – Drain Charge          | $I_D = 250A$                                                                                                                          |     | 360  |     |      |
| $T_{d(on)}$  | Turn-on Delay Time           | <b>Inductive switching @ <math>125^\circ\text{C}</math></b><br>$V_{GS} = 15V$<br>$V_{Bus} = 66V$<br>$I_D = 250A$<br>$R_G = 2.5\Omega$ |     | 80   |     | ns   |
| $T_r$        | Rise Time                    |                                                                                                                                       |     | 165  |     |      |
| $T_{d(off)}$ | Turn-off Delay Time          |                                                                                                                                       |     | 280  |     |      |
| $T_f$        | Fall Time                    |                                                                                                                                       |     | 135  |     |      |
| $E_{on}$     | Turn-on Switching Energy     | <b>Inductive switching @ <math>25^\circ\text{C}</math></b><br>$V_{GS} = 15V, V_{Bus} = 66V$<br>$I_D = 250A, R_G = 2.5\Omega$          |     | 1.1  |     | mJ   |
| $E_{off}$    | Turn-off Switching Energy    |                                                                                                                                       |     | 1.2  |     |      |
| $E_{on}$     | Turn-on Switching Energy     | <b>Inductive switching @ <math>125^\circ\text{C}</math></b><br>$V_{GS} = 15V, V_{Bus} = 66V$<br>$I_D = 250A, R_G = 2.5\Omega$         |     | 1.22 |     | mJ   |
| $E_{off}$    | Turn-off Switching Energy    |                                                                                                                                       |     | 1.28 |     |      |

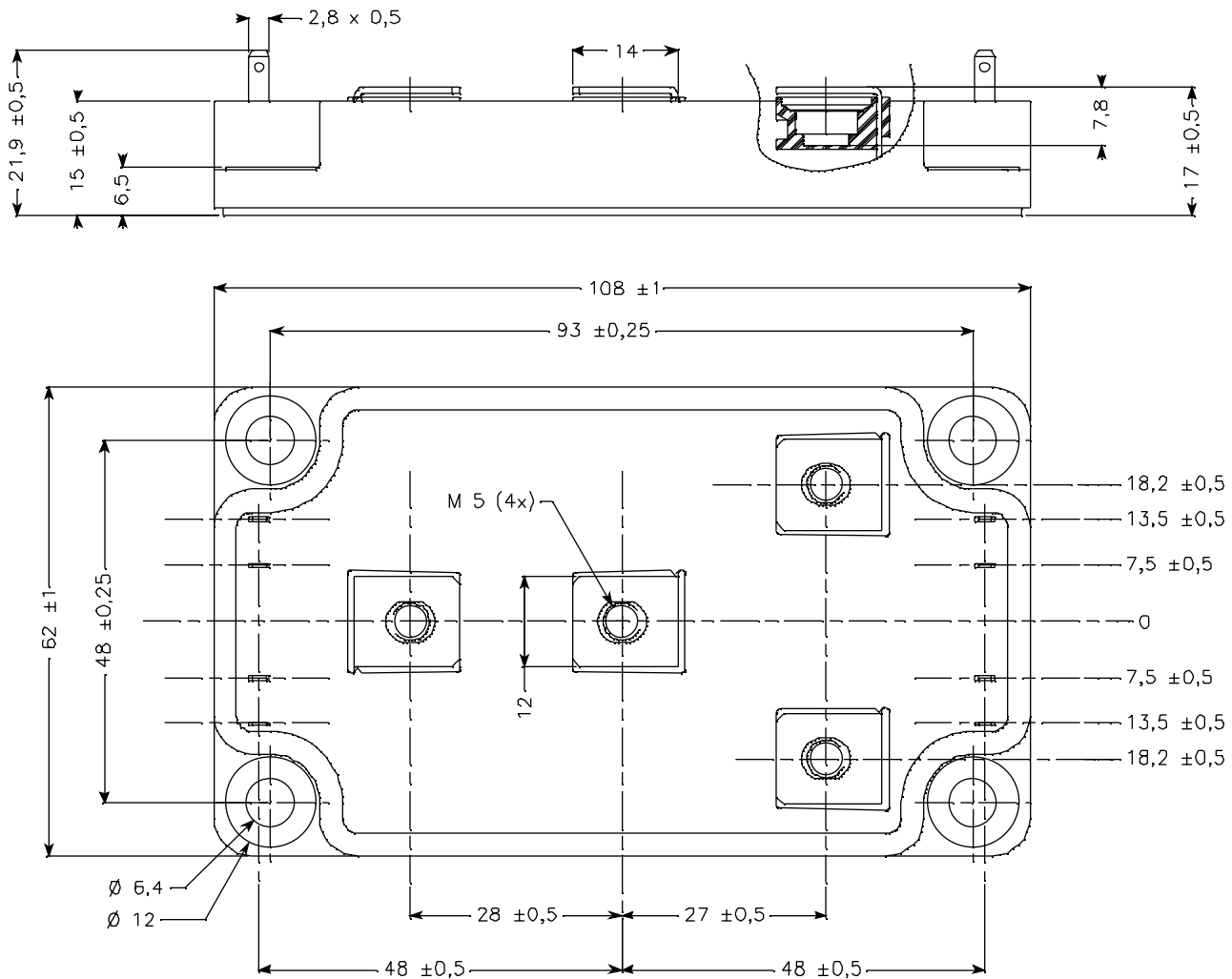
**Diode ratings and characteristics**

| Symbol           | Characteristic                          | Test Conditions                                                  |                        | Min | Typ  | Max | Unit |
|------------------|-----------------------------------------|------------------------------------------------------------------|------------------------|-----|------|-----|------|
| V <sub>RRM</sub> | Maximum Peak Repetitive Reverse Voltage |                                                                  |                        | 200 |      |     | V    |
| I <sub>RM</sub>  | Maximum Reverse Leakage Current         | V <sub>R</sub> =200V                                             | T <sub>j</sub> = 25°C  |     |      | 350 | μA   |
|                  |                                         |                                                                  | T <sub>j</sub> = 125°C |     |      | 600 |      |
| I <sub>F</sub>   | DC Forward Current                      |                                                                  | T <sub>c</sub> = 80°C  |     | 200  |     | A    |
| V <sub>F</sub>   | Diode Forward Voltage                   | I <sub>F</sub> = 200A                                            |                        |     | 1    |     | V    |
|                  |                                         | I <sub>F</sub> = 400A                                            |                        |     | 1.4  |     |      |
|                  |                                         | I <sub>F</sub> = 200A                                            | T <sub>j</sub> = 125°C |     | 0.9  |     |      |
| t <sub>rr</sub>  | Reverse Recovery Time                   | I <sub>F</sub> = 200A<br>V <sub>R</sub> = 133V<br>di/dt =400A/μs | T <sub>j</sub> = 25°C  |     | 60   |     | ns   |
|                  | T <sub>j</sub> = 125°C                  |                                                                  |                        | 110 |      |     |      |
| Q <sub>rr</sub>  | Reverse Recovery Charge                 |                                                                  | T <sub>j</sub> = 25°C  |     | 400  |     | nC   |
|                  |                                         |                                                                  | T <sub>j</sub> = 125°C |     | 1680 |     |      |

## Thermal and package characteristics

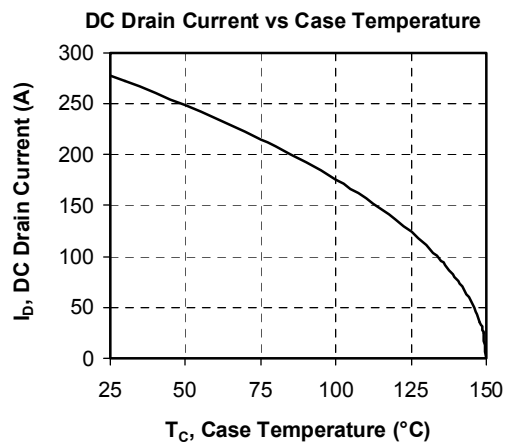
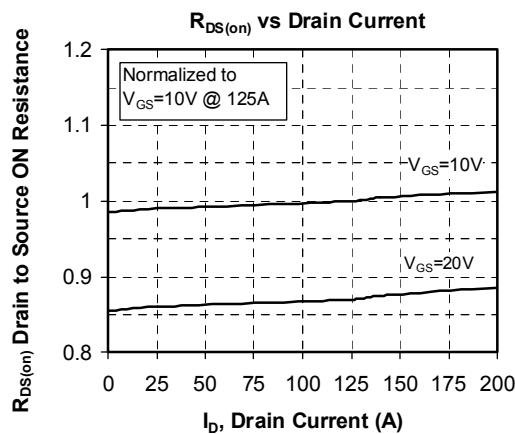
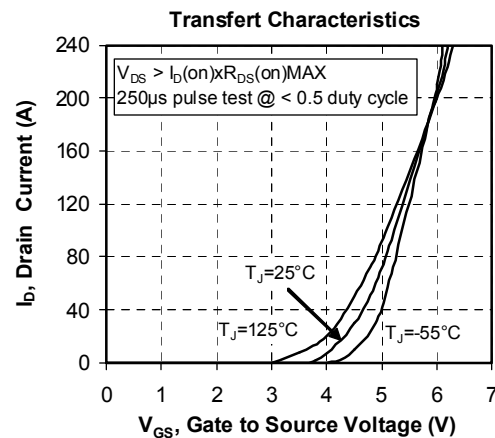
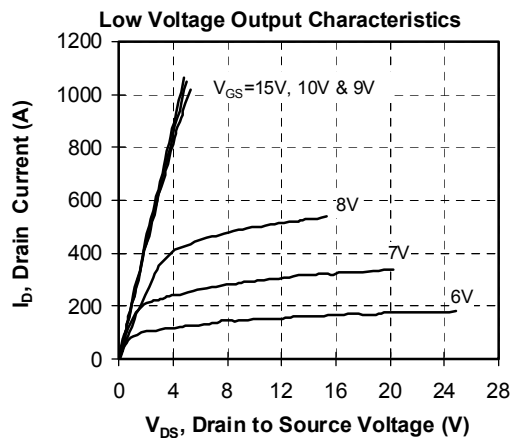
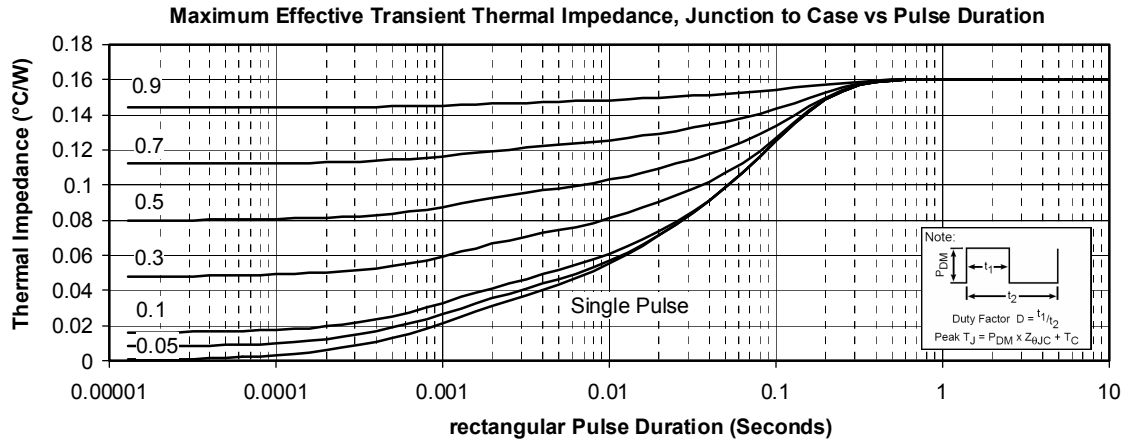
| Symbol     | Characteristic                                                                  | Min           | Typ | Max  | Unit |
|------------|---------------------------------------------------------------------------------|---------------|-----|------|------|
| $R_{thJC}$ | Junction to Case Thermal Resistance                                             | transistor    |     | 0.16 | °C/W |
|            |                                                                                 | diode         |     | 0.29 |      |
| $V_{ISOL}$ | RMS Isolation Voltage, any terminal to case $t=1$ min, $I_{isol}<1mA$ , 50/60Hz | 2500          |     |      | V    |
| $T_J$      | Operating junction temperature range                                            | -40           |     | 150  | °C   |
| $T_{STG}$  | Storage Temperature Range                                                       | -40           |     | 125  |      |
| $T_C$      | Operating Case Temperature                                                      | -40           |     | 100  |      |
| Torque     | Mounting torque                                                                 | To heatsink   | M6  | 3    | N.m  |
|            |                                                                                 | For terminals | M5  | 2    |      |
| Wt         | Package Weight                                                                  |               |     | 280  | g    |

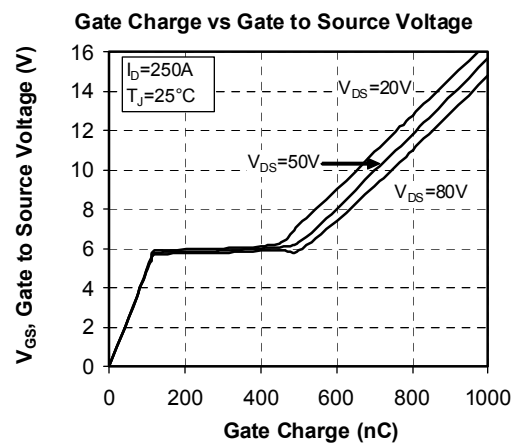
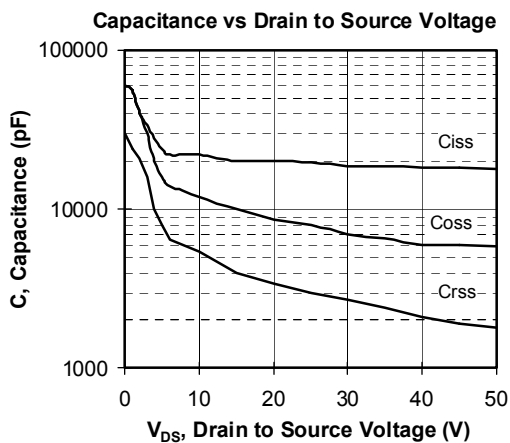
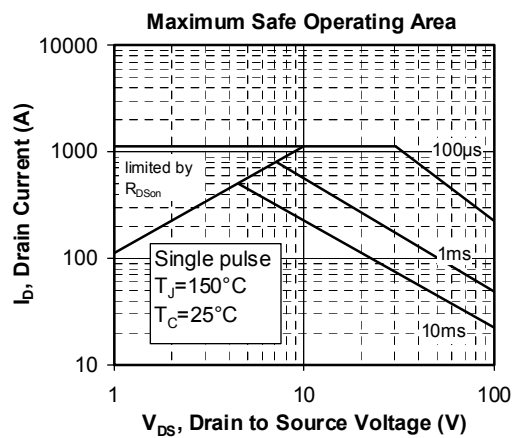
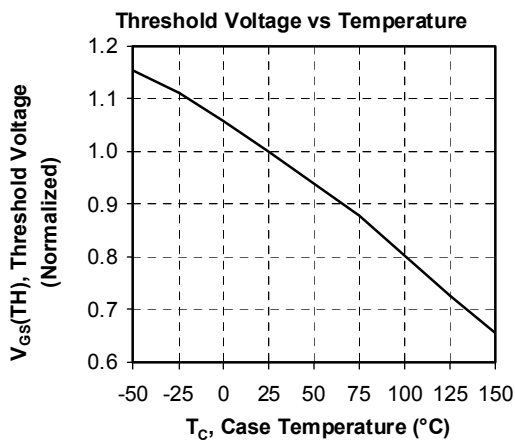
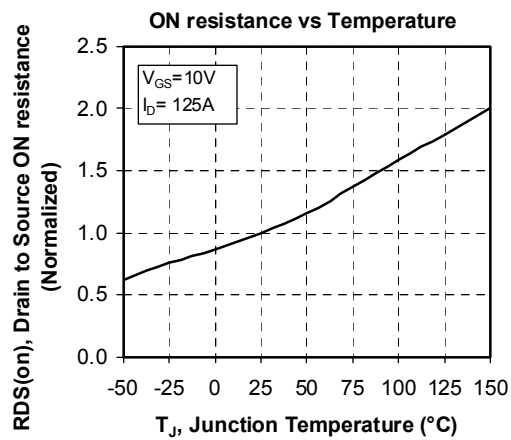
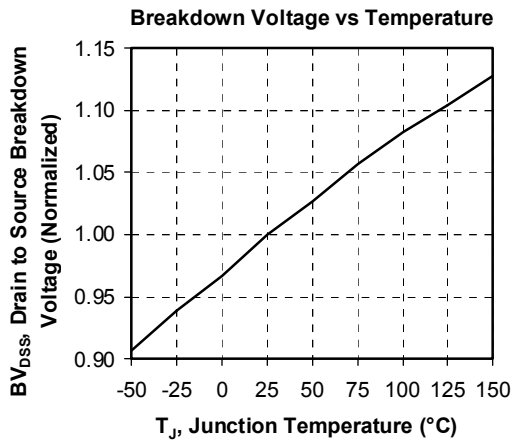
## SP6 Package outline (dimensions in mm)



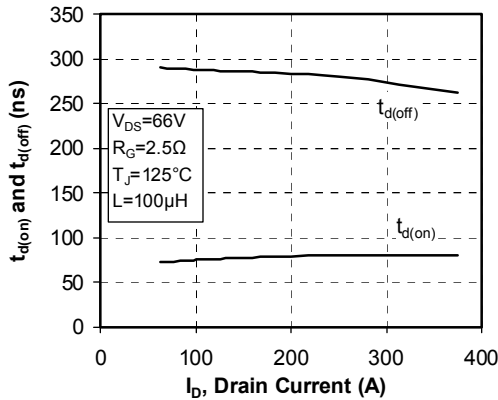
See application note APT0601 - Mounting Instructions for SP6 Power Modules on [www.microsemi.com](http://www.microsemi.com)

## Typical Performance Curve

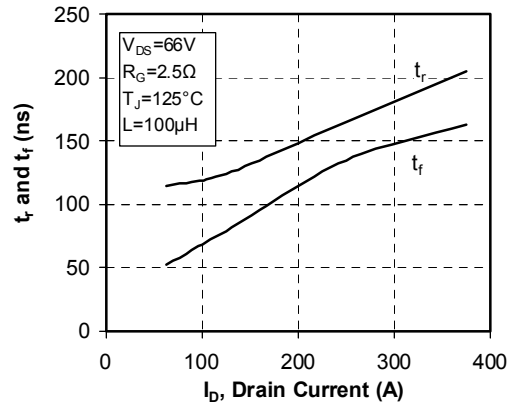




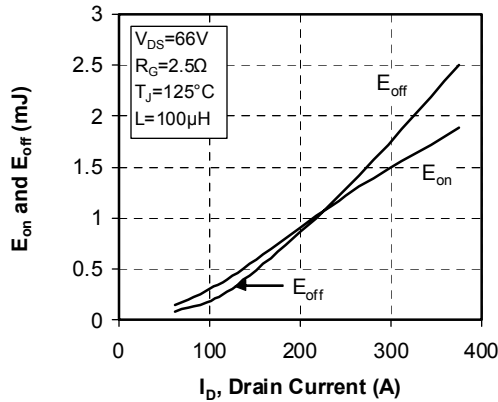
Delay Times vs Current



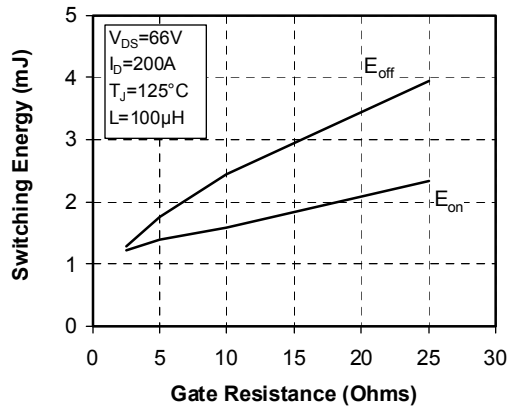
Rise and Fall times vs Current



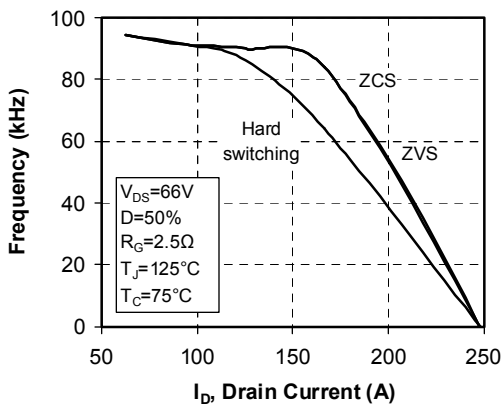
Switching Energy vs Current



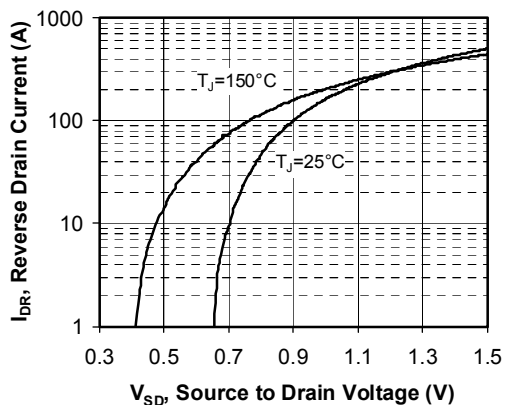
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.